







# Locked mode thresholds and EFA with applied error fields

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#### NSTX Results Review for FY2004 Run

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### Goals of XPs 415 & 455

- XP 415 Parametric dependence of low-density lockedmode threshold
  - Find locking threshold vs. density and  $B_{\rm T}$
  - Compare external to internal sensor signature
  - Measure rotation profile during locked phase
- XP 455 Error-field studies using tearing modes and mode control coils
  - Try to modify locking during  $I_{\rm P}$  ramp with RWM coils
    - Vary coil current amplitude and polarity
    - Determine threshold density vs. applied B-field
  - Extend results into flat-top (started)
    - Extend coil current pulse and scan coil current amplitude

#### XP415: $I_P$ ramp-up LM threshold near $\overline{n}_e = 1.2 \times 10^{19} \text{ m}^{-3}$

- Had to avoid early H-mode to get mode to lock at 3kG
- Rotating mode locks later w/o sufficient NBI



#### Toroidal phase data from sensors offers clues into EF



Data suggests island locked with O-point near Z=0,  $\phi_{\text{ENG}} \approx 130^{\circ} \Rightarrow \text{apply} \pm B_{\text{R}} \text{ at } \phi_{\text{ENG}} \approx 240^{\circ} \text{ (H/I)}$ 1.5 1.5 1.5  $\phi_{\rm F} = 310^{\circ}$  $\phi_{\rm E} = 220^{\circ}$  $\phi_{\rm F} = 130^{\circ}$ 1.0 1.0 1.0 B<sub>R</sub><0 B<sub>R</sub>>0 0.5 0.5 0.5 Z(m) Z(m) **B**<sub>R</sub>>0 0.0 0.0 0.0 -0.5 -0.5 -0.5 ⊔<sub>В</sub><0  $B_R > 0$ -1.0 -1.0 -1.0 -1.5 -1.5 -1.5 0.2 0.4 0.6 0.8 1.0 1.2 1.4 1.6 0.4 0.6 0.8 1.0 1.2 1.4 1.6 0.2 0.4 0.6 0.8 1.0 1.2 1.4 0.2 1.6 R(m) R(m)

R(m)

# Two external mode control coils used for mode locking & error field studies



- 1kA I<sub>RWM</sub> ⇒ 10G of n=1 radial field @ external B<sub>R</sub> sensors
- n=3 amplitude similar @ ext. sensors, but w/ much faster radial fall-off into plasma





Locked-mode shots also demonstrate error field amplification (EFA) dependence on  $\beta_N$  at low-n<sub>e</sub>



Internal sensors find only n=1 EFA

n=1 EFA factor ≈ 2-3 at maximum β<sub>N</sub>
n=2 and n=3 EFA weak or absent



## Summary of results from XP 415

Parametric dependence of low-density locked-mode threshold

- $B_T$  scan with 1MA PF1B LSN and early NBI:
  - Ramp-up locked mode stable at 140ms for all fields tried (3-4.5kG) when plasma achieved early H-mode @ 100ms
    - True even with reduce density prior to transition
  - With density very low prior to normal transition, H-mode transition could be avoided and locked-mode excited at 3kG
    - Did not test  $B_T$  scaling in this condition (due to 3kG limit)
- Locking of rotating mode @ 200ms sensitive to P<sub>NBI</sub>
  - Need 2MW or above to keep mode from locking
  - Likely evidence of rotation (torque) threshold
    - Have CHERS data, not in MDS+ yet

# Summary of results from XP 455

**Error-field studies using tearing modes and mode control coils** 

- Started from LM target developed in XP415
  - Toroidal position of installed coils chosen based on toroidal phase of locked-modes during I<sub>P</sub> ramp-up (prior to XP455)
    - a.k.a. educated guess from external LM sensors
- Locking density threshold depends on sign of I<sub>RWM</sub>
  - Sign of current consistent with correcting transient EF
    - Possible shift of plate and/or vessel conductor magnetic center
- Error field amplification measured at higher  $\beta_{\text{N}}$ 
  - Later during I<sub>P</sub> ramp, toroidal phase of error field changes, and "corrective" RWM field apparently becomes error field.
  - External & internal sensors measure 2-3× n=1 amplification
    - Little or no internal n=2 or n=3 amplification of applied EF observed